

Plastic Medium-Power Complementary Silicon Transistors

... designed for general-purpose amplifier and low-speed switching applications.

- High DC Current Gain —
 $h_{FE} = 2500$ (Typ) @ I_C
 $= 4.0$ Adc
- Collector-Emitter Sustaining Voltage — @ 100 mAdc
 $V_{CEO(sus)} = 60$ Vdc (Min) — TIP120, TIP125
 $= 80$ Vdc (Min) — TIP121, TIP126
 $= 100$ Vdc (Min) — TIP122, TIP127
- Low Collector-Emitter Saturation Voltage —
 $V_{CE(sat)} = 2.0$ Vdc (Max) @ $I_C = 3.0$ Adc
 $= 4.0$ Vdc (Max) @ $I_C = 5.0$ Adc
- Monolithic Construction with Built-In Base-Emitter Shunt Resistors
- TO-220AB Compact Package

***MAXIMUM RATINGS**

| Rating | Symbol | TIP120, TIP125 | TIP121, TIP126 | TIP122, TIP127 | Unit |
|---|----------------|----------------|----------------|----------------|------------------------------|
| Collector-Emitter Voltage | V_{CEO} | 60 | 80 | 100 | Vdc |
| Collector-Base Voltage | V_{CB} | 60 | 80 | 100 | Vdc |
| Emitter-Base Voltage | V_{EB} | 5.0 | | | Vdc |
| Collector Current — Continuous Peak | I_C | 5.0 8.0 | | | Adc |
| Base Current | I_B | 120 | | | mAdc |
| Total Power Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C | P_D | 65 0.52 | | | Watts W/ $^\circ\text{C}$ |
| Total Power Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C | P_D | 2.0 0.016 | | | Watts W/ $^\circ\text{C}$ |
| Unclamped Inductive Load Energy (1) | E | 50 | | | mJ |
| Operating and Storage Junction, Temperature Range | T_J, T_{stg} | -65 to +150 | | | $^\circ\text{C}$ |

THERMAL CHARACTERISTICS

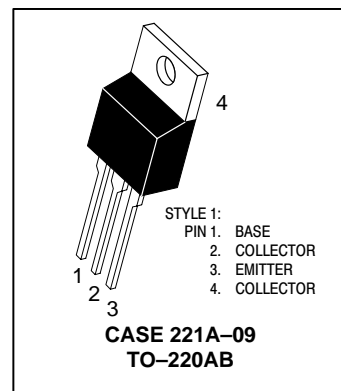
| Characteristic | Symbol | Max | Unit |
|---|-----------------|------|--------------------|
| Thermal Resistance, Junction to Case | $R_{\theta JC}$ | 1.92 | $^\circ\text{C/W}$ |
| Thermal Resistance, Junction to Ambient | $R_{\theta JA}$ | 62.5 | $^\circ\text{C/W}$ |

(1) $I_C = 1$ A, $L = 100$ mH, P.R.F. = 10 Hz, $V_{CC} = 20$ V, $R_{BE} = 100 \Omega$.

NPN
TIP120*
TIP121*
TIP122*
PNP
TIP125*
TIP126*
TIP127*

*ON Semiconductor Preferred Device

DARLINGTON
5 AMPERE
COMPLEMENTARY SILICON
POWER TRANSISTORS
60-80-100 VOLTS
65 WATTS



Preferred devices are ON Semiconductor recommended choices for future use and best overall value.

TIP120 TIP121 TIP122 TIP125 TIP126 TIP127

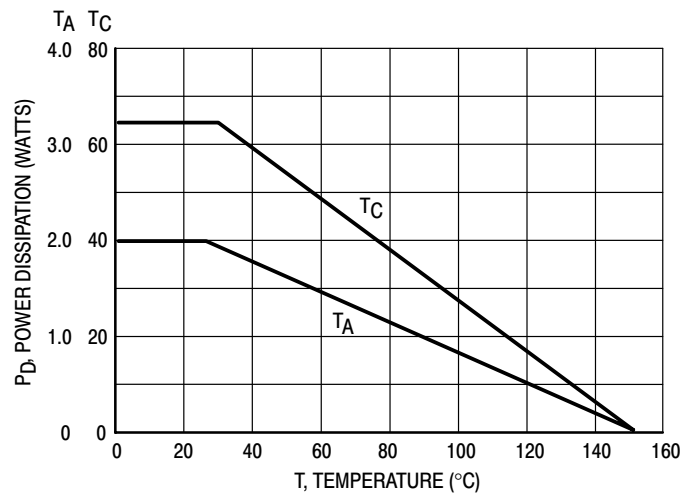


Figure 1. Power Derating

TIP120 TIP121 TIP122 TIP125 TIP126 TIP127

ELECTRICAL CHARACTERISTICS ($T_C = 25^\circ\text{C}$ unless otherwise noted)

| Characteristic | Symbol | Min | Max | Unit |
|---|---------------|-----------------|-------------------|------|
| OFF CHARACTERISTICS | | | | |
| Collector–Emitter Sustaining Voltage (1) ($I_C = 100\text{ mAdc}$, $I_B = 0$) | $V_{CE(sus)}$ | 60 80 100 | — | Vdc |
| Collector Cutoff Current ($V_{CE} = 30\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 40\text{ Vdc}$, $I_B = 0$) ($V_{CE} = 50\text{ Vdc}$, $I_B = 0$) | I_{CEO} | — — — | 0.5 0.5 0.5 | mAdc |
| Collector Cutoff Current ($V_{CB} = 60\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 80\text{ Vdc}$, $I_E = 0$) ($V_{CB} = 100\text{ Vdc}$, $I_E = 0$) | I_{CBO} | — — — | 0.2 0.2 0.2 | mAdc |
| Emitter Cutoff Current ($V_{BE} = 5.0\text{ Vdc}$, $I_C = 0$) | I_{EBO} | — | 2.0 | mAdc |

ON CHARACTERISTICS (1)

| | | | | |
|--|---------------|--------------|------------|-----|
| DC Current Gain ($I_C = 0.5\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) ($I_C = 3.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) | h_{FE} | 1000 1000 | — — | — |
| Collector–Emitter Saturation Voltage ($I_C = 3.0\text{ Adc}$, $I_B = 12\text{ mAdc}$) ($I_C = 5.0\text{ Adc}$, $I_B = 20\text{ mAdc}$) | $V_{CE(sat)}$ | — — | 2.0 4.0 | Vdc |
| Base–Emitter On Voltage ($I_C = 3.0\text{ Adc}$, $V_{CE} = 3.0\text{ Vdc}$) | $V_{BE(on)}$ | — | 2.5 | Vdc |

DYNAMIC CHARACTERISTICS

| | | | | |
|--|----------|--------|------------|----|
| Small–Signal Current Gain ($I_C = 3.0\text{ Adc}$, $V_{CE} = 4.0\text{ Vdc}$, $f = 1.0\text{ MHz}$) | h_{fe} | 4.0 | — | — |
| Output Capacitance ($V_{CB} = 10\text{ Vdc}$, $I_E = 0$, $f = 0.1\text{ MHz}$) | C_{ob} | — — | 300 200 | pF |

(1) Pulse Test: Pulse Width $\leq 300\ \mu\text{s}$, Duty Cycle $\leq 2\%$.

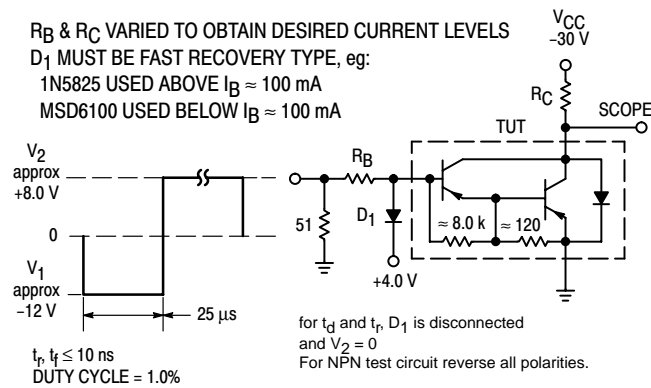


Figure 2. Switching Times Test Circuit

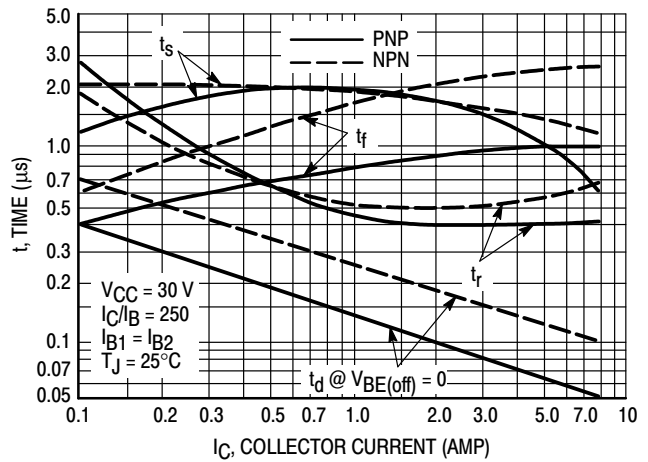


Figure 3. Switching Times

TIP120 TIP121 TIP122 TIP125 TIP126 TIP127

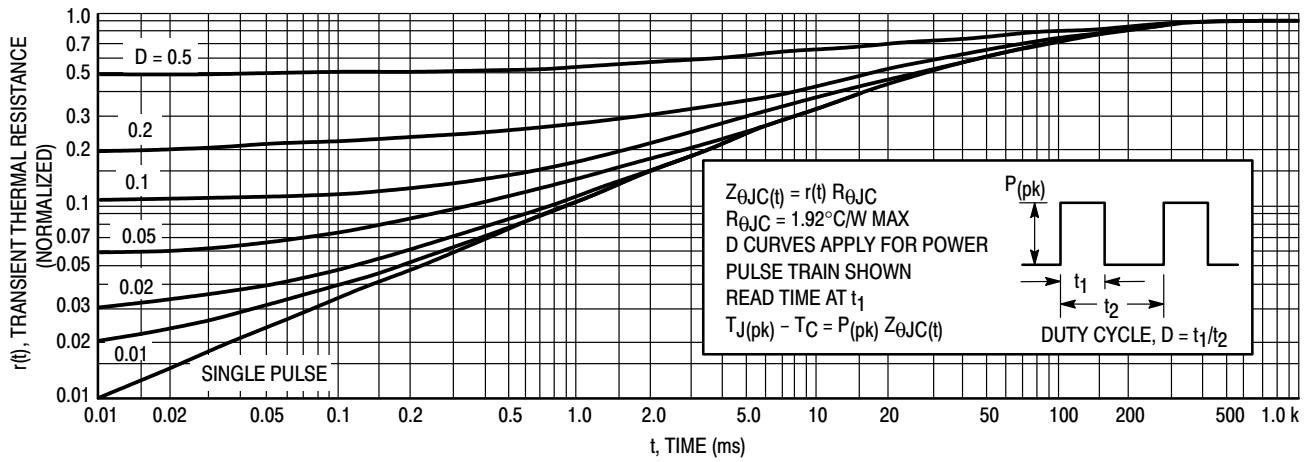


Figure 4. Thermal Response

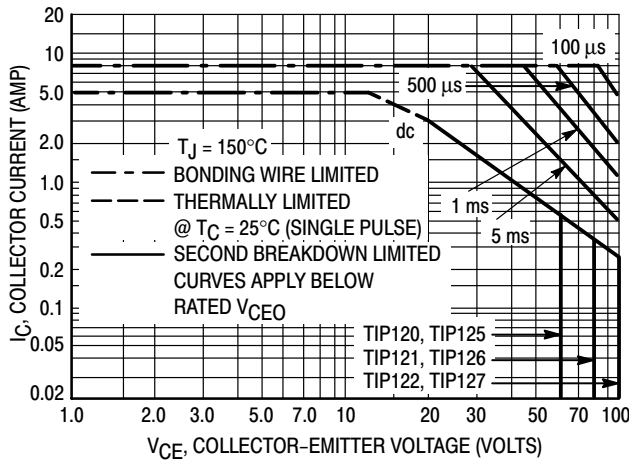


Figure 5. Active-Region Safe Operating Area

There are two limitations on the power handling ability of a transistor: average junction temperature and second breakdown. Safe operating area curves indicate $I_C - V_{CE}$ limits of the transistor that must be observed for reliable operation, i.e., the transistor must not be subjected to greater dissipation than the curves indicate.

The data of Figure 5 is based on $T_J(pk) = 150^\circ\text{C}$; T_C is variable depending on conditions. Second breakdown pulse limits are valid for duty cycles to 10% provided $T_J(pk) < 150^\circ\text{C}$. $T_J(pk)$ may be calculated from the data in Figure 4. At high case temperatures, thermal limitations will reduce the power that can be handled to values less than the limitations imposed by second breakdown

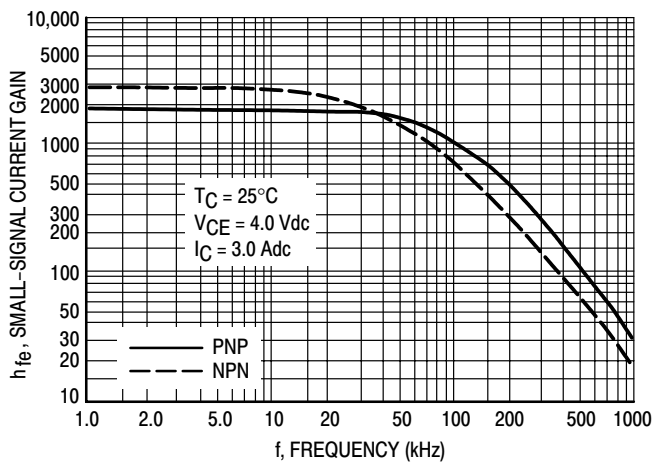


Figure 6. Small-Signal Current Gain

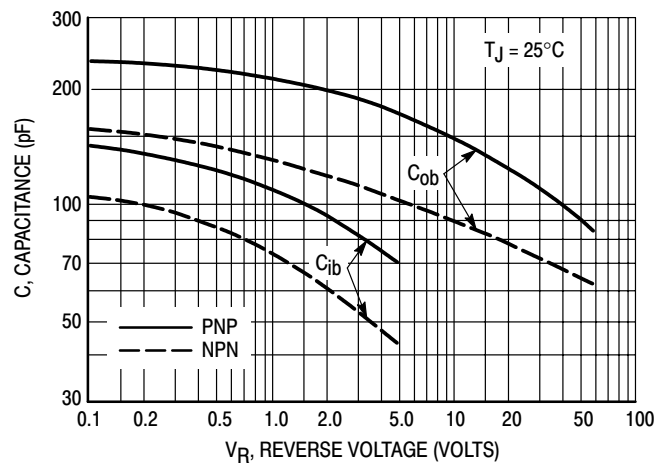
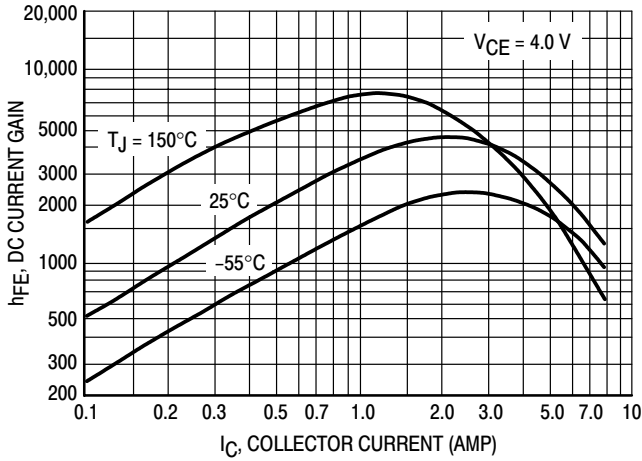


Figure 7. Capacitance

TIP120 TIP121 TIP122 TIP125 TIP126 TIP127

NPN
TIP120, TIP121, TIP122



PNP
TIP125, TIP126, TIP127

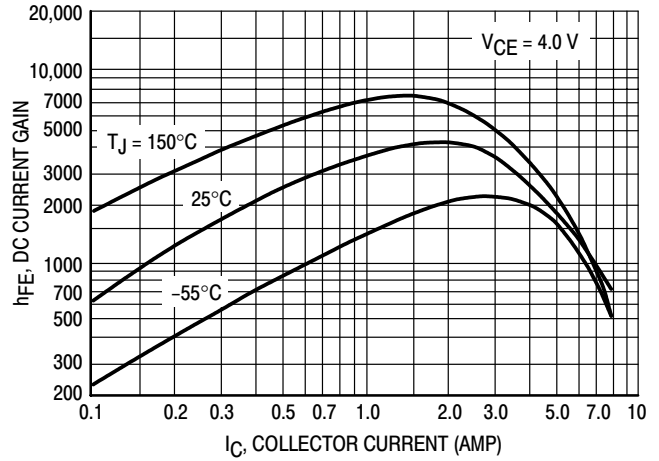


Figure 8. DC Current Gain

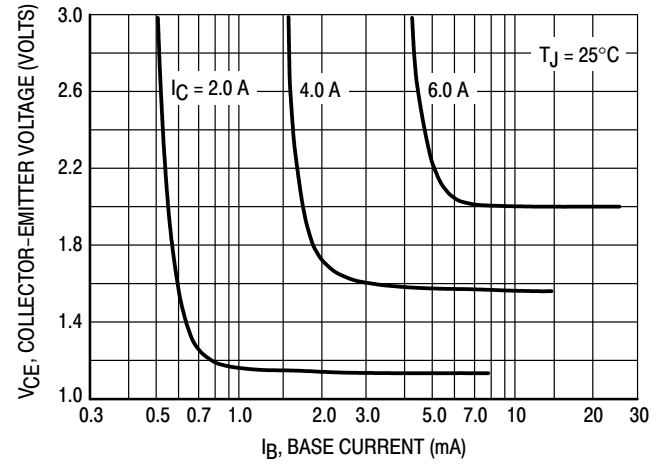
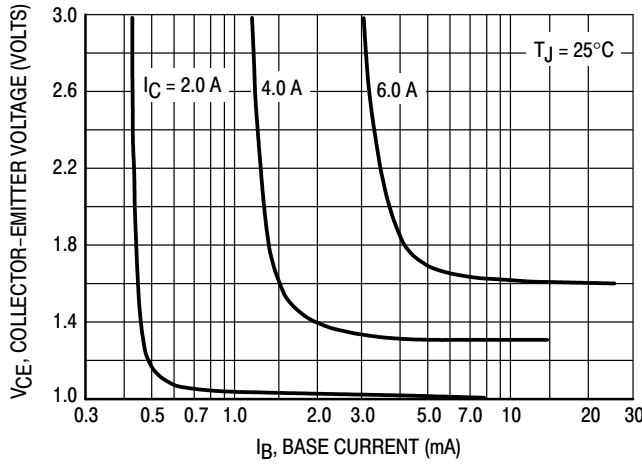


Figure 9. Collector Saturation Region

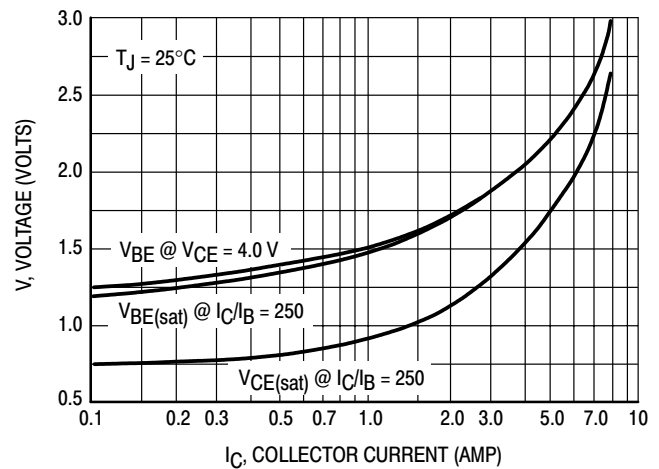
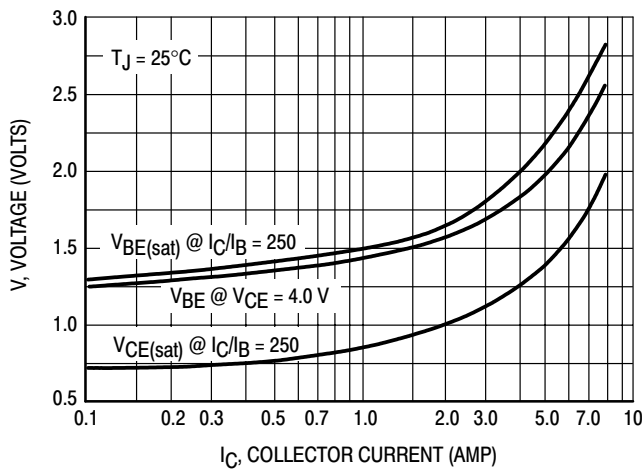
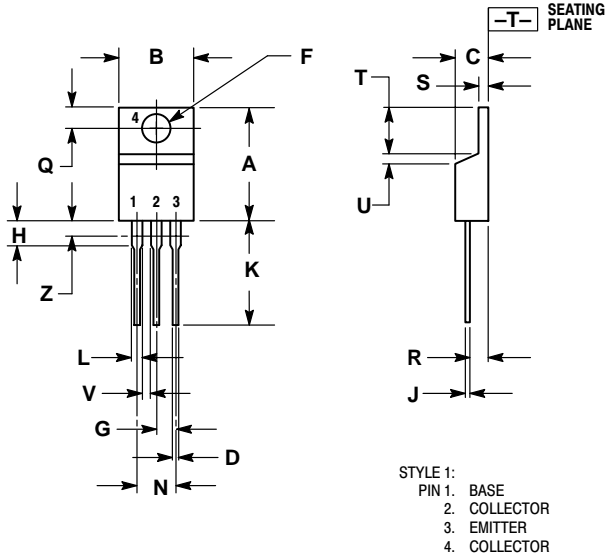


Figure 10. "On" Voltages

TIP120 TIP121 TIP122 TIP125 TIP126 TIP127

PACKAGE DIMENSIONS

TO-220AB
CASE 221A-09
ISSUE AA



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

| DIM | INCHES | | MILLIMETERS | |
|-----|--------|-------|-------------|-------|
| | MIN | MAX | MIN | MAX |
| A | 0.570 | 0.620 | 14.48 | 15.75 |
| B | 0.380 | 0.405 | 9.66 | 10.28 |
| C | 0.160 | 0.190 | 4.07 | 4.82 |
| D | 0.025 | 0.035 | 0.64 | 0.88 |
| F | 0.142 | 0.147 | 3.61 | 3.73 |
| G | 0.095 | 0.105 | 2.42 | 2.66 |
| H | 0.110 | 0.155 | 2.80 | 3.93 |
| J | 0.018 | 0.025 | 0.46 | 0.64 |
| K | 0.500 | 0.562 | 12.70 | 14.27 |
| L | 0.045 | 0.060 | 1.15 | 1.52 |
| N | 0.190 | 0.210 | 4.83 | 5.33 |
| Q | 0.100 | 0.120 | 2.54 | 3.04 |
| R | 0.080 | 0.110 | 2.04 | 2.79 |
| S | 0.045 | 0.055 | 1.15 | 1.39 |
| T | 0.235 | 0.255 | 5.97 | 6.47 |
| U | 0.000 | 0.050 | 0.00 | 1.27 |
| V | 0.045 | --- | 1.15 | --- |
| Z | --- | 0.080 | --- | 2.04 |

Notes

ON Semiconductor and  are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly or indirectly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer.

PUBLICATION ORDERING INFORMATION

Literature Fulfillment:

Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada
Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada
Email: ONlit@hibbertco.com

N. American Technical Support: 800-282-9855 Toll Free USA/Canada

JAPAN: ON Semiconductor, Japan Customer Focus Center
4-32-1 Nishi-Gotanda, Shinagawa-ku, Tokyo, Japan 141-0031
Phone: 81-3-5740-2700
Email: r14525@onsemi.com

ON Semiconductor Website: <http://onsemi.com>

For additional information, please contact your local Sales Representative.